UMW AOD508

30V N-Channel MOSFET

1.Description

- Very Low $R_{DS(ON)}$ at 10 V_{GS}
- Low Gate Charge
- High Current Capability

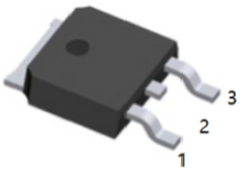
2.Features

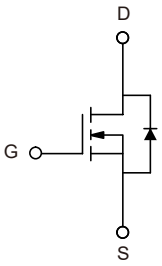
- $V_{DS\ (V)}$=30V
- I_D=70A(V_{GS}=10V)
- $R_{DS(ON)}$<3mΩ(V_{GS}=10V)
- $R_{DS(ON)}$<4.5mΩ(V_{GS}=4.5V)

3.Pinning information

Pin	Symbol	Description
1	G	GATE
3	S	SOURCE
2	D	DRAIN

TO-252(DPAK)
top view





4.Absolute Maximum Ratings T_A= 25°C

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current [G]	T_C=25°C	I_D	70	A
	T_C=100°C		55	
Pulsed Drain Current [c]		I_{DM}	159	
Continuous Drain Current	T_A=25°C	I_{DSM}	22	
	T_A=70°C		18	
Avalanche Current [c]		I_{AS}	37	
Avalanche energy L=0.1mH [c]		E_{AS}	68	mJ
V_{DS} Spike	100ns	V_{SPIKE}	36	V
Power Dissipation [B]	T_C=25°C	P_D	50	W
	T_C=100°C		25	
Power Dissipation [A]	T_A=25°C	P_{DSM}	2.5	
	T_A=70°C		1.6	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

5.Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient	t ≤ 10s	$R_{\theta JA}$	16	20	°C/W
Maximum Junction-to-Ambient	Steady-State		41	50	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	2.1	3	°C/W

6.Electrical Characteristic (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
		T_J=55°C			5	μA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.2	1.8	2.2	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A		2.4	3	mΩ
		V_{GS}=4.5V, I_D=20A		3.3	4.5	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=20A		105		S
Diode Forward Voltage	V_{SD}	I_S=1A, V_{GS}=0V		0.7	1	V
Maximum Body-Diode Continuous Current	I_S				58	A
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=15V, f=1MHz		2010		pF
Output Capacitance	C_{oss}			898		pF
Reverse Transfer Capacitance	C_{rss}			124		pF
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.9	1.8	2.7	Ω
Total Gate Charge	Q_g(10V)	V_{GS}=10V, V_{DS}=15V, I_D=20A		36	49	nC
Total Gate Charge	Q_g(4.5V)			17	23	nC
Gate Source Charge	Q_{gs}			6		nC
Gate Drain Charge	Q_{gd}			8		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω		7.5		ns
Turn-On Rise Time	t_r			4		ns
Turn-Off DelayTime	$t_{D(off)}$			37		ns
Turn-Off Fall Time	t_f			7.5		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F=20A, dI/dt=500A/μs		14		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=20A, dI/dt=500A/μs		20.3		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(MAX)}$=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature $T_{J(MAX)}$=175°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

7.1Typical characteristic

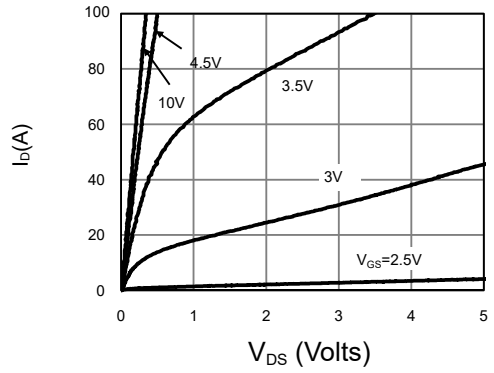


Fig 1: On-Region Characteristics (Note E)

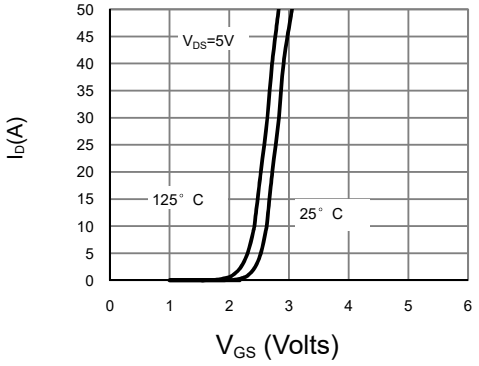


Figure 2: Transfer Characteristics (Note E)

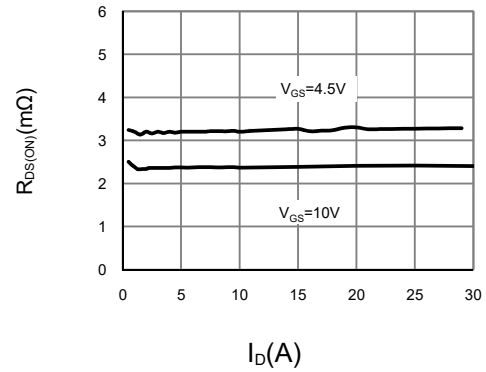


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

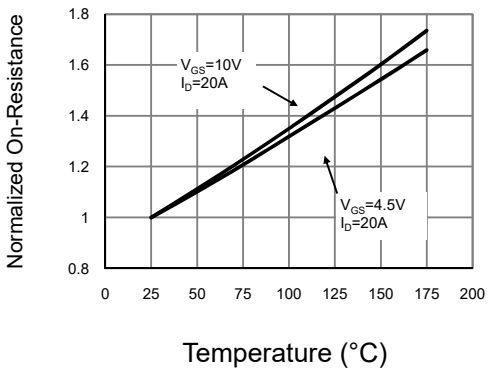


Figure 4: On-Resistance vs. Junction Temperature (Note E)

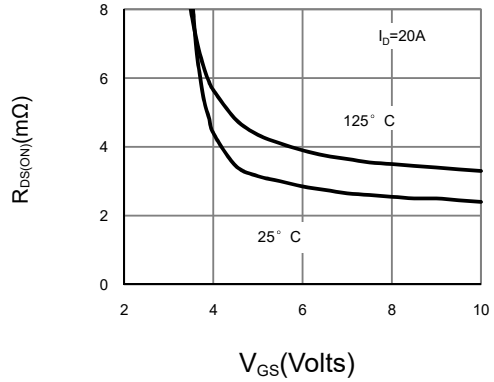


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

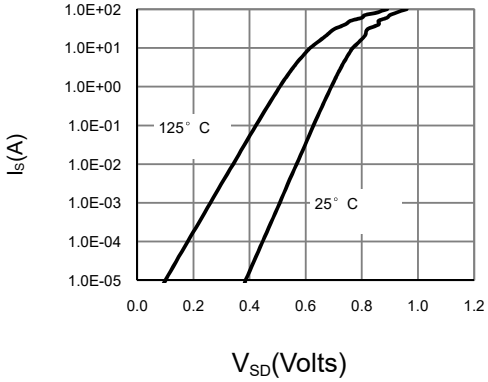


Figure 6: Body-Diode Characteristics(Note E)

7.2Typical characteristic

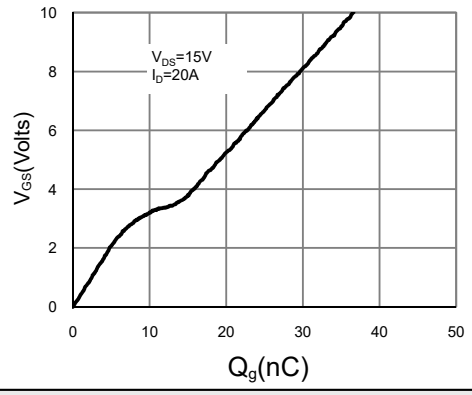


Figure 7: Gate-Charge Characteristics

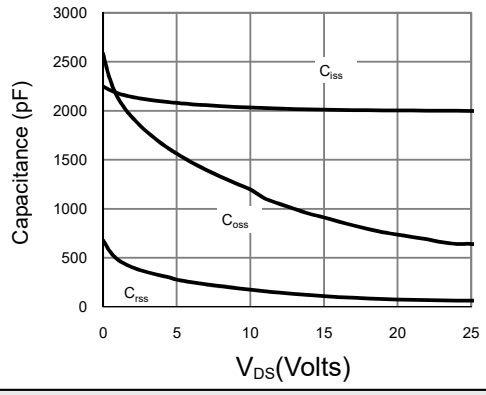


Figure 8: Capacitance Characteristics

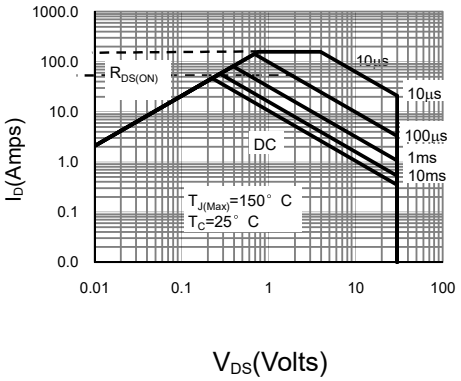


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

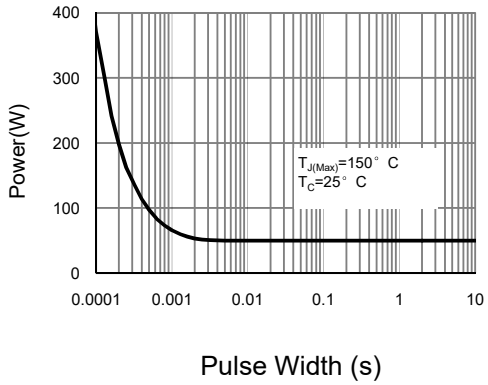


Figure 10: Single Pulse Power Rating Junction-to Case (Note F)

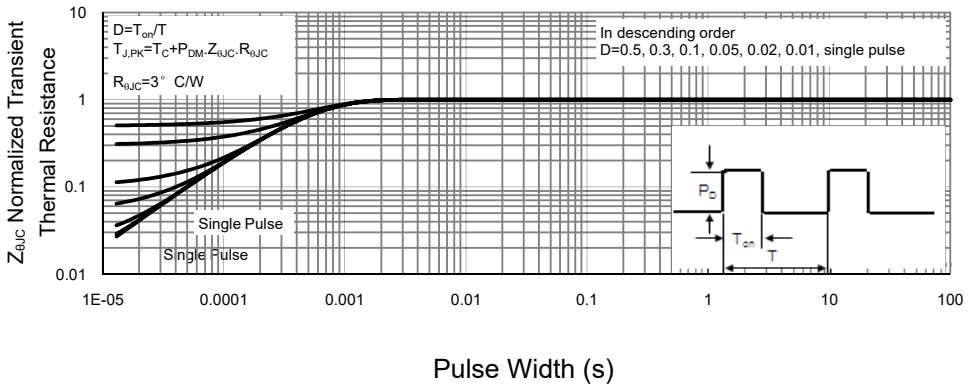


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

7.3Typical characteristic

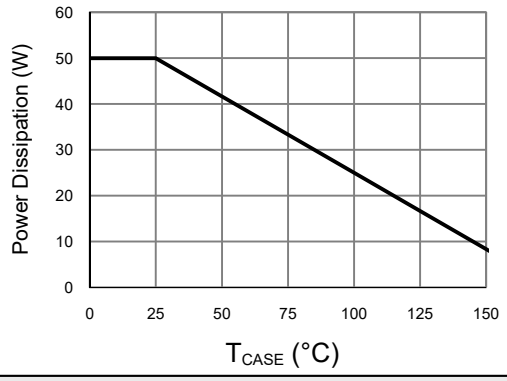


Figure 12: Power De-rating (Note F)

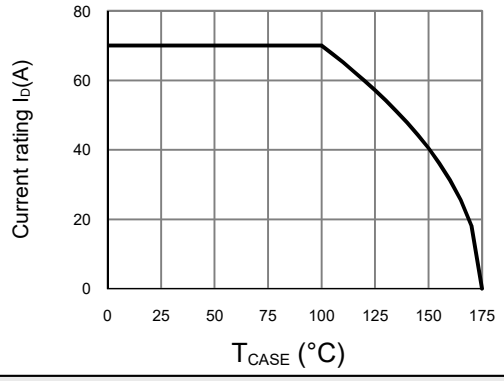


Figure 13: Current De-rating (Note F)

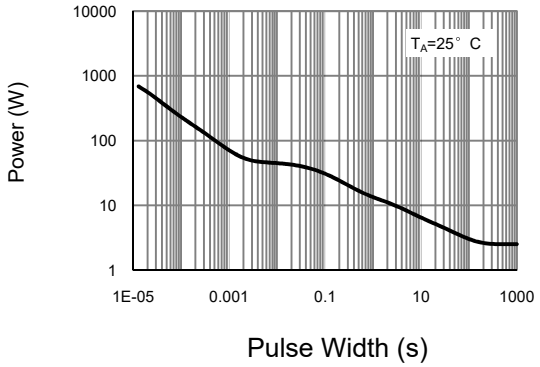


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

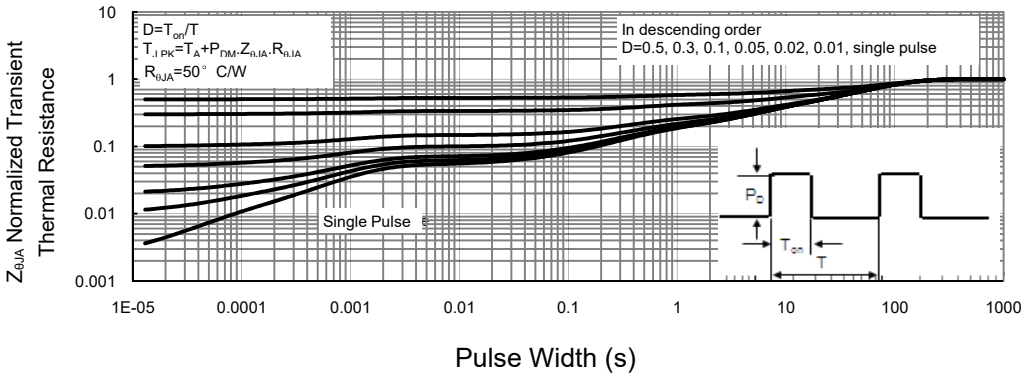
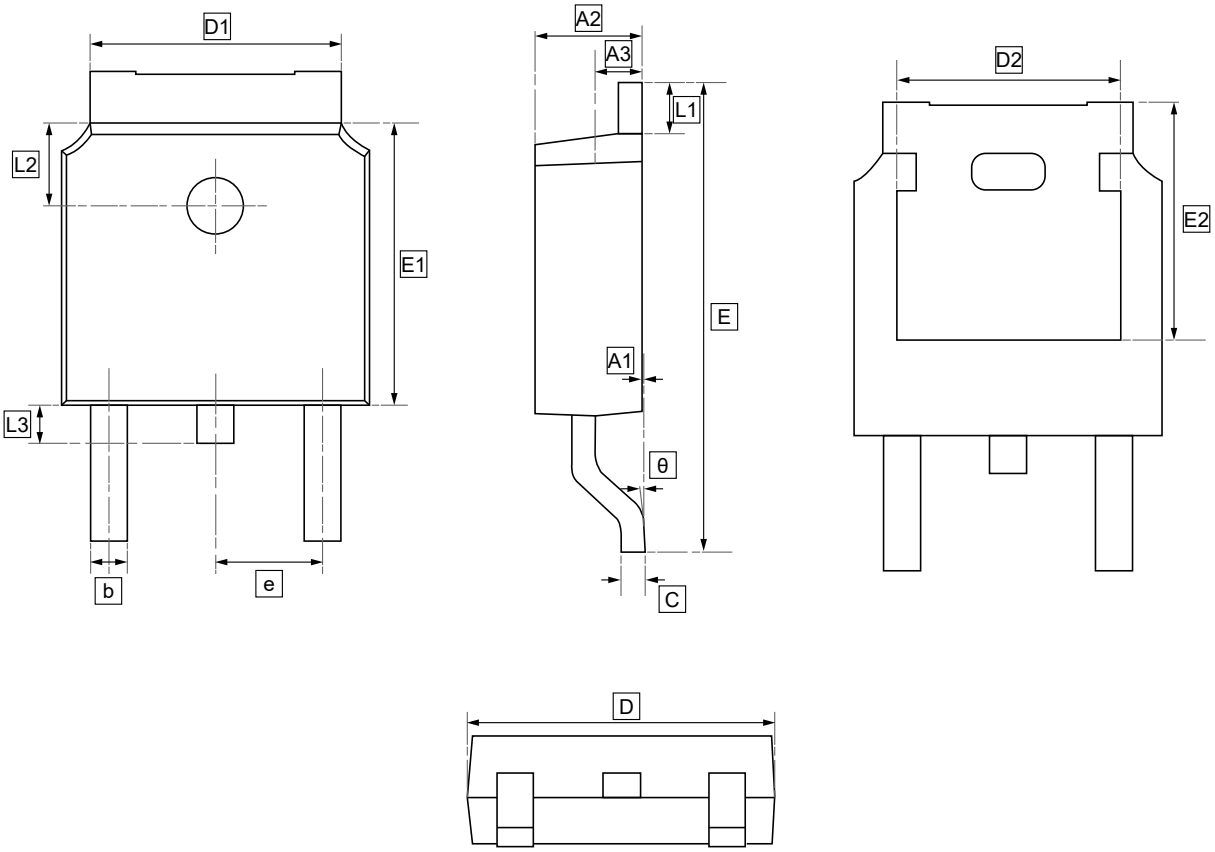


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

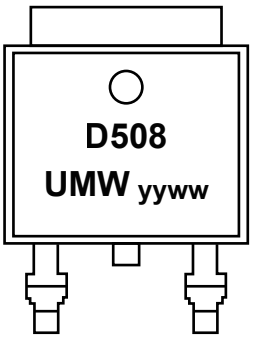
8.TO-252 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A1	A2	A3	b	c	D	D1	D2	E	E1	E2	e	L1	L2	L3	θ
Min	0.00	2.18	0.90	0.65	0.46	6.35	4.95	4.32	9.40	5.97	5.21	2.286	0.89	1.70	0.60	0.00
Max	0.13	2.39	1.10	0.85	0.61	6.73	5.46	4.90	10.41	6.22	5.38	BSC	1.27	1.90	1.00	8.00

9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW AOD508	TO-252	2500	Tape and reel

10.Disclaimer

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